

2SP0115T2A0-FF900R12ME7_B11 and 2SP0115T2A0C-FF900R12ME7_B11 Data Sheet

Compact, high-performance, plug-and-play dual-channel IGBT driver based on SCALE[™]-2 technology for individual and parallel-connected modules

Abstract

The SCALETM-2 plug-and-play driver 2SP0115T2A0-FF900R12ME7_B11 / 2SP0115T2A0C-FF900R12ME7_B11 (Coated version using ELPEGUARD SL 1307 FLZ/2 from Lackwerke Peters with a typical thickness of 50 μ m) is a compact dual-channel intelligent gate driver designed for Infineon's EconoDUALTM IGBTs FF900R12ME7_B11. The driver features an electrical interface with a built-in DC/DC power supply.

For drivers adapted to other types of high-power and high-voltage IGBT modules, refer to

www.power.com/gate-driver/go/plug-and-play

Features	Applications
 Plug-and-play solution Allows parallel connection of IGBT modules Shortens application development time Extremely reliable; long service life Built-in DC/DC power supply 20-pin flat cable interface Duty cycle 0 100% Active clamping of V_{ce} at turn-off IGBT short-circuit protection Monitoring of supply voltage Safe isolation to EN 50178 UL compliant 	 Wind-power converters Industrial drives UPS Power-factor correctors Traction Railroad power supplies Welding SMPS Radiology and laser technology Research and many others
 Suitable for FF900R12ME7_B11 	

EconoDUAL is a trademark of Infineon Technologies AG, Munich



Safety Notice!

The data contained in this data sheet is intended exclusively for technically trained staff. Handling all high-voltage equipment involves risk to life. Strict compliance with the respective safety regulations is mandatory!

Any handling of electronic devices is subject to the general specifications for protecting electrostatic-sensitive devices according to international standard IEC 60747-1, Chapter IX or European standard EN 100015 (i.e. the workplace, tools, etc. must comply with these standards). Otherwise, this product may be damaged.

Important Product Documentation

This data sheet contains only product-specific data. For a detailed description, must-read application notes and common data that apply to the whole series, please refer to "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers" on www.power.com/gate-driver/qo/2SP0115T.

When applying SCALE-2 plug-and-play drivers, please note that these drivers are specifically adapted to a particular type of IGBT module. Therefore, the type designation of SCALE-2 plug-and-play drivers also includes the type designation of the corresponding IGBT module. These drivers are not valid for IGBT modules other than those specified. Incorrect use may result in failure.

Mechanical Dimensions

Dimensions: Refer to "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers" Mounting principle: Soldered onto EconoDUAL[™] module FF900R12ME7_B11

Absolute Maximum Ratings

Parameter	Remarks	Min	Мах	Unit
Supply voltage V _{CC}	VCC to GND	0	16	V
Logic input and output voltages	To GND	-0.5	VCC+0.	5 V
SO _x current	Fault condition, total current		20	mA
Gate peak current Iout	Note 1	-8	+15	А
Average supply current I_{CC}	Note 2		290	mA
Output power per gate	Ambient temperature \leq 70°C (Note 3)		1.2	W
	Ambient temperature \leq 85°C (Note 3)		1	W
Switching frequency f			4	kHz
Test voltage (50Hz/1min.)	Primary to secondary (Note 16)		3800	V _{AC(eff)}
	Secondary to secondary (Note 16)		3800	V _{AC(eff)}
DC-link voltage	Note 4		800	V
dV/dt	Rate of change of input to output voltage		50	kV/µs
Operating voltage	Primary/secondary, secondary/secondary		1200	Vpeak



Parameter	Remarks	Min	Max	Unit
Operating temperature	Note 20	-20	85	°C
Storage temperature	Note 21	-40	50	°C
Surface temperature	Only 2SP0115T2A0C-FF900R12ME7_B11 (Note 22)		125	°C

Recommended Operating Conditions

Parameter	Remarks	Min	Тур	Max	Unit
Supply voltage V _{CC} Resistance from TB to GND SO _x current	To GND Blocking time ≠ 0, ext. value Fault condition, 3.3V logic	14.5 128	15	15.5 ∞ 4	V kΩ mA

Electrical Characteristics

Power Supply	Remarks	Min	Тур	Max	Unit
Supply current Icc	Without load		33		mA
Efficiency η	Internal DC/DC converter		85		%
Coupling capacitance Cio	Primary side to secondary side, total, per	channel	23		pF
Power Supply Monitoring	Remarks	Min	Тур	Max	Unit
Supply threshold Vcc	Primary side, clear fault	11.9	12.6	13.3	V
	Primary side, set fault (Note 5)	11.3	12.0	12.7	V
Monitoring hysteresis	Primary side, set/clear fault	0.35			V
Supply threshold V _{isox} -V _{eex}	Secondary side, clear fault	12.1	12.6	13.1	V
	Secondary side, set fault (Note 6)	11.5	12.0	12.5	V
Monitoring hysteresis	Secondary side, set/clear fault	0.35			V
Supply threshold Veex-VCOMx	Secondary side, clear fault	5	5.15	5.3	V
	Secondary side, set fault (Note 6)	4.7	4.85	5	V
Monitoring hysteresis	Secondary side, set/clear fault	0.15			V
Logic Inputs and Outputs	Remarks	Min	Тур	Max	Unit
Input impedance	V(INx) > 3V (Note 7)	3.5	4.1	4.6	kΩ
Turn-on threshold	V(INx) (Note 8)		2.6		V
Turn-off threshold	V(INx) (Note 8)		1.3		V
SOx output voltage	Fault condition, I(SOx) < 8mA			0.7	V



Vce-monitoring threshold Response time DC-link voltage > 550V (Note 9)10.2VResponse time DC-link voltage > 550V (Note 9)4.9 μ sDelay to IGBT turn-off Blocking timeAfter the response time (Note 10)0.2 μ sBlocking timeAfter fault (Note 11)90msTiming CharacteristicsRemarksMinTypMaxUnitTurn-on delay ta(m) Note 12Note 1275nsTurn-off delay ta(m) Note 18Note 18 ± 2 nsOutput rise time tr(out) Gx to Ex (Note 13)5nsOutput fall time tr(out) Gx to Ex (Note 13)10nsDead time transmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-onf gate resistor Rg(m) Gate voltage at turn-onf Gate voltage at turn-onf Gate voltage at turn-onf Gate resistance to COMxNote 150.675 Ω Electrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s) Partial discharge extinction volt.Primary to secondary side (Note 16) Secondary to secondary side (Note 17)380038503900VerfSecondary to secondary side Primary to secondary side12.6mmMmVpeakClearance distancePrimary to secondary side12.6mmMmMmPrimary to secondary side6.6mmPrimary to secondary side12.6mm	Short-circuit Protection	Remarks	Min	Тур	Max	Unit
Delay to IGBT turn-off Blocking timeAfter the response time (Note 10)0.2μsBlocking timeAfter fault (Note 11)90msTiming CharacteristicsRemarksMinTypMaxUnitTurn-off delay ta(on) Dutput factoringNote 1275nsTurn-off delay ta(on) Dutput rise time tr(out)Note 18±2nsJitter of turn-off delay Dutput rise time tr(out)Gx to Ex (Note 13)5nsOutput file time tr(out) Gx to Ex (Note 13)10nspaseDutput file time tr(out) Turn-off delay time tr(out)Gx to Ex (Note 13)10nsDead time between outputs Transmission delay of fault stateHalf-bridge mode (Note 19)3µsJitter of dead time Turn-off gate resistor Rg(on) Gate voltage at turn-on Gate voltage at turn-on P=0W0.675ΩΩGate voltage at turn-onf Gate voltage at turn-onf Secondary to secondary side (Note 16)380038503900VerTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 17)380038503900VerPartial discharge extinction volt.Primary to secondary side (Note 17)1200 Loce Primary to secondary side (Note 17)Wax Loce Loce Primary to secondary side12.6mmGearance distancePrimary to secondary side6.6mmGate voltage12.6mmGearance distancePrimary to secondary side6.6mmMmYerekClearance distanceP	Vce-monitoring threshold	Between auxiliary terminals		10.2		V
Blocking timeAfter fault (Note 11)90msTiming CharacteristicsRemarksMinTypMaxUnitTurn-on delay ta(on)Note 1265nsTurn-off delay ta(on)Note 1265nsJitter of turn-ond felayNote 18±2nsJitter of turn-off delayNote 18±4nsOutput rise time tr(out)Gx to Ex (Note 13)5nsOutput fill time tr(out)Gx to Ex (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3µsJitter of dead timeHalf-bridge mode±50nsTransmission delay of fault stateNote 150.675ΩOutputsRemarksMinTypMaxTurn-ong ate resistor Rq(on)Note 150.675ΩTurn-off gate resistor Rq(off)Note 152.05ΩGate-voltage at turn-offP=0W-9.2VP=1.2W-7.1VGate resistance to COMx4.7KΩElectrical IsolationRemarksMinTypMaxPartial discharge extinction volt.Primary to secondary side (Note 16)380038503900VerrSecondary to secondary side (Note 17)1200VpeakVpeakCreepage distancePrimary to secondary side (Note 17)1200VpeakClearance distancePrimary to secondary side6.6mmPrimary to secondary side6.6mmSecondary side6.6 <td>Response time</td> <td>DC-link voltage > 550V (Note 9)</td> <td></td> <td>4.9</td> <td></td> <td>μs</td>	Response time	DC-link voltage > 550V (Note 9)		4.9		μs
Timing CharacteristicsRemarksMinTypMaxUnitTurn-on delay ta(on)Note 1275nsTurn-onf delay ta(on)Note 1265nsJitter of turn-onf delayNote 18±2nsJitter of turn-onf delayNote 18±4nsOutput rise time tr(out)Gx to Ex (Note 13)5nsOutput fall time tr(out)Gx to Ex (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3µsJitter of dead timeHalf-bridge mode±50nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor Rg(on)Note 150.675ΩTurn-off gate resistor Rg(on)Note 150.675ΩGate voltage at turn-offP=0W-9.2VP=1.2W-7.1VGate resistor Rg(on)Note 15Test voltage (50Hz/1s)Primary to secondary side (Note 16)380038503900VerrPartial discharge extinction volt.Primary to secondary side (Note 17)1220VVpeakCreepage distancePrimary to secondary side (Note 17)1200VpeakVpeakClearance distancePrimary to secondary side6.6mmMmPrimary to secondary side6.6mmSecondary side6.6mm	Delay to IGBT turn-off	After the response time (Note 10)		0.2		μs
Turn-on delay $t_{d(on)}$ Note 1275nsTurn-off delay $t_{d(off)}$ Note 1265nsJitter of turn-on delayNote 18 ± 2 nsJitter of turn-off delayNote 18 ± 4 nsOutput rise time $t_{(out)}$ Gx to E_x (Note 13)5nsOutput fall time $t_{f(out)}$ Gx to E_x (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3µsJitter of dead timeHalf-bridge mode (Note 19)3µsJitter of dead timeHalf-bridge mode ± 50 nsTransmission delay of fault stateNote 150.675 Ω OutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Note 152.05 Ω Gate voltage at turn-on15Vgate-voltage at turn-on15VGate resistance to COMxP=0W-9.2VP=1.2W7.1VTest voltage (50Hz/1s)Primary to secondary side (Note 16)380038503900VerfPartial discharge extinction volt.Primary to secondary side (Note 17)1200VpeakCreepage distancePrimary to secondary side (Note 17)1200VpeakPrimary to secondary side12.6mmSecondary to secondary side12.6Clearance distancePrimary to secondary side6.6mmSecondary to secondary side6.6	Blocking time	After fault (Note 11)		90		ms
Turn-off delay t _{d(off)} Note 1265nsJitter of turn-on delayNote 18±2nsJitter of turn-off delayNote 18±4nsOutput rise time t _{r(out)} G _x to E _x (Note 13)5nsOutput fall time t _(out) G _x to E _x (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3µsJitter of dead timeHalf-bridge mode (Note 19)3µsTransmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor R _{g(on)} Note 150.675ΩTurn-off gate resistor R _{g(on)} Note 150.675ΩGate-voltage at turn-on15VP=1.2WGate-voltage at turn-offP=0W-9.2VP=1.2W-7.1VGate resistance to COMx4.7kΩElectrical IsolationRemarksMinTypMaxUnitTest voltage extinction volt.Primary to secondary side (Note 16)380038503900VerfSecondary to secondary side (Note 17)1220VereakVereakSecondary to secondary side (Note 17)1200VereakVereakCreepage distancePrimary to secondary side (Note 17)12.6mmPrimary to secondary side6.6mmSecondary to secondary side6.6Clearance distancePrimary to secondary side6.6mmPrimary to secondary side6.6 <th>Timing Characteristics</th> <th>Remarks</th> <th>Min</th> <th>Тур</th> <th>Max</th> <th>Unit</th>	Timing Characteristics	Remarks	Min	Тур	Max	Unit
Jitter of turn-on delayNote 18 ± 2 nsJitter of turn-off delayNote 18 ± 4 nsOutput rise time $t_{(out)}$ Gx to Ex (Note 13)5nsOutput fall time $t_{(out)}$ Gx to Ex (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3 μs Jitter of dead timeHalf-bridge mode ± 50 nsTransmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Note 150.675 Ω Turn-off gate resistor $R_{g(on)}$ Note 152.05 Ω Gate voltage at turn-on15VGate resistance to COMx4.7 $K\Omega$ Electrical IsolationRemarksMinTypPartial discharge extinction volt.Primary to secondary side (Note 16)38003850Partial discharge extinction volt.Primary to secondary side (Note 17)120 V_{peak} Creepage distancePrimary to secondary side12.6mmPrimary to secondary side6.6mmmmClearance distancePrimary to secondary side12.3mmClearance distancePrimary to secondary side6.6mm	Turn-on delay t _{d(on)}	Note 12		75		ns
Jitter of turn-off delayNote 18 ± 4 nsOutput rise time $t_{(out)}$ Gx to Ex (Note 13)5nsOutput fall time $t_{(out)}$ Gx to Ex (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3 μ sJitter of dead timeHalf-bridge mode (Note 19)3 μ sTransmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Note 150.675 Ω Turn-off gate resistor $R_{g(on)}$ Note 152.05 Ω Gate voltage at turn-on15VGate voltage at turn-offP=0W-9.2VP=1.2W-7.1VGate resistance to COMx4.7K Ω Electrical IsolationRemarksMinTypMaxPartial discharge extinction volt.Primary to secondary side (Note 16)380038503900VerfSecondary to secondary side (Note 17)1200VpeakVpeakCreepage distancePrimary to secondary side (Note 17)1200VpeakCreepage distancePrimary to secondary side6.6mmPrimary to secondary side6.6mmmmPrimary to secondary side6.6mmPrimary to secondary side6.6mm	Turn-off delay t _{d(off)}	Note 12		65		ns
Output rise time $t_{r(out)}$ Gx to Ex (Note 13)5nsOutput fall time $t_{r(out)}$ Gx to Ex (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3 μ sJitter of dead timeHalf-bridge mode \pm 50nsTransmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Note 15 0.675 Ω Turn-off gate resistor $R_{g(on)}$ Note 15 2.05 Ω Gate voltage at turn-on15 V $P=1.2W$ Gate voltage at turn-offP=0W -9.2 V P=1.2W -7.1 V Gate resistance to COMxKemarksMinTypMaxTest voltage (50Hz/1s)Primary to secondary side (Note 16)380038503900 V_{eff} Partial discharge extinction volt.Primary to secondary side (Note 17)1220 V_{peak} Creepage distancePrimary to secondary side (Note 17)1200 V_{peak} Creepage distancePrimary to secondary side (Note 17)12.6mmPrimary to secondary side6.6mmmmPrimary to secondary side6.6mmPrimary to secondary side6.6mm	Jitter of turn-on delay	Note 18		±2		ns
Output fall time $t_{(totr)}$ Dead time between outputsGx to E_x (Note 13)10nsDead time between outputsHalf-bridge mode (Note 19)3 μs Jitter of dead timeHalf-bridge mode ± 50 nsTransmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Note 15 2.05 Ω Turn-off gate resistor $R_{g(off)}$ Note 15 2.05 Ω Gate voltage at turn-on15VGate resistance to COMx -7.1 VElectrical IsolationRemarksMinTypTest voltage (50Hz/1s)Primary to secondary side (Note 16)380038503900Partial discharge extinction volt.Primary to secondary side (Note 17)1220VPartial discharge extinction volt.Primary to secondary side (Note 17)1200VCreepage distancePrimary to secondary side12.6mmPrimary to Secondary side12.6mmprimary to secondary side12.6Creepage distancePrimary to secondary side12.6mmPrimary to NTC6.5mmprimary to secondary side12.3Clearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mmSecondary to secondary side6.6	Jitter of turn-off delay	Note 18		±4		ns
Dead time between outputs Jitter of dead time Transmission delay of fault stateHalf-bridge mode (Note 19) Half-bridge mode3 μs DutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{g(on)}$ Turn-off gate resistor $R_{g(off)}$ Gate voltage at turn-on Gate voltage at turn-on Gate voltage at turn-off P=0W P=1.2WNote 15 2.050.6775 2.05 Ω Ω Ψ P=1.2WElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 17) Secondary to secondary side (Note 17) Secondary to secondary side Secondary to secondary side<	Output rise time tr(out)	G _x to E _x (Note 13)		5		ns
Jitter of dead time Transmission delay of fault stateHalf-bridge mode Note 14 ± 50 nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor $R_{q(on)}$ Gate voltage at turn-on Gate voltage at turn-off P=0W P=1.2WNote 15 2.050.675 2.05 Ω Gate voltage at turn-off Gate-voltage at turn-off Bet voltage at turn-off P=0W P=1.2WP=0W -9.2 -7.1 VVGate resistance to COMxRemarksMinTypMaxUnitElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 17) Secondary to secondary side Secondary to secondary side (Note 17) Secondary to secondary side Secondary to secondary side (Note 17) T200Vpeak Vpeak MmCreepage distancePrimary to secondary side Primary to secondary side Secondary to secondary s	Output fall time $t_{f(out)}$	G _x to E _x (Note 13)		10		ns
Transmission delay of fault stateNote 14400nsOutputsRemarksMinTypMaxUnitTurn-on gate resistor Rg(on)Note 150.675ΩTurn-off gate resistor Rg(off)Note 152.05ΩGate voltage at turn-on15VGate-voltage at turn-onfP=0W-9.2VP=1.2W-7.1VGate resistance to COMx4.7kΩElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 17)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17)1220VVpeakCreepage distancePrimary to secondary side6.6mmmmmmClearance distancePrimary to secondary side6.6mmmmPrimary to secondary side6.6mmmmmmSecondary to secondary side6.6mmmmPrimary to secondary side6.6mmmmPrimary to secondary side6.6mmPrimary to secondary side6.6mm	Dead time between outputs	Half-bridge mode (Note 19)		3		μs
OutputsRemarksMinTypMaxUnitTurn-on gate resistor Rg(on)Note 150.675ΩTurn-off gate resistor Rg(off)Note 152.05ΩGate voltage at turn-on15VGate-voltage at turn-offP=0W-9.2VP=1.2W-7.1VGate resistance to COMx4.7KΩElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 17) Secondary to secondary side (Note 17) <b< td=""><td>Jitter of dead time</td><td>Half-bridge mode</td><td></td><td>±50</td><td></td><td>ns</td></b<>	Jitter of dead time	Half-bridge mode		±50		ns
Turn-on gate resistor $R_{g(on)}$ Note 150.675 Ω Turn-off gate resistor $R_{g(off)}$ Note 152.05 Ω Gate voltage at turn-on15VGate-voltage at turn-offP=0W-9.2VP=1.2W-7.1VGate resistance to COMx4.7k Ω Electrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17)1220VpeakCreepage distancePrimary to secondary side12.6mmPrimary to secondary side6.6mmCreepage distancePrimary to secondary side12.6mmPrimary to secondary side6.6mmSecondary to secondary side6.6mm	Transmission delay of fault state	Note 14		400		ns
Turn-off gate resistor $R_{g(off)}$ Gate voltage at turn-on Gate-voltage at turn-offNote 152.05 Ω 15 V V P=0W P=1.2W -9.2 V P=1.2WGate resistance to COMxP=0W P=1.2W -9.2 V P=1.2W -7.1 V Secondary side (Note 16) Secondary side (Note 16) 3800 3850 3900 V_{eff} Test voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 17) 3800 3850 3900 V_{eff} Partial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17) 1220 V_{peak} Creepage distancePrimary to secondary side 6.6 mmPrimary to NTC 6.5 mmClearance distancePrimary to secondary side 12.3 mmClearance distancePrimary to secondary side 6.6 mm	Outputs	Remarks	Min	Тур	Max	Unit
Gate voltage at turn-on Gate-voltage at turn-offP=0W P=0W P=1.2W15V -9.2Gate resistance to COMx-9.2V P=1.2WV -7.1V VElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 16)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17)1220VpeakCreepage distancePrimary to secondary side12.6mm MmPrimary to NTC6.5mm MmClearance distancePrimary to secondary side12.3mm mm Secondary to secondary side	Turn-on gate resistor R _{g(on)}	Note 15		0.675		Ω
Gate-voltage at turn-off $P=0W$ $P=1.2W$ -9.2 -7.1 V V -7.1 Gate resistance to COMxRemarksMinTypMaxUnitElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 16)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17)1220 1200VpeakCreepage distancePrimary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side6.6mm	Turn-off gate resistor Rg(off)	Note 15		2.05		Ω
P=1.2W-7.1VGate resistance to COMx4.7kΩElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 16)380038503900VerffPartial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17)1220VpeakCreepage distancePrimary to secondary side12.6mmPrimary to secondary side6.6mmClearance distancePrimary to secondary side6.5mmClearance distancePrimary to secondary side6.6mmPrimary to secondary side6.6mmmmSecondary to secondary side6.6mmMinary	Gate voltage at turn-on			15		V
Gate resistance to COMx4.7kΩElectrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 16) Secondary to secondary side (Note 16) Secondary to secondary side (Note 17) Secondary to secondary side	Gate-voltage at turn-off	P=0W		-9.2		V
Electrical IsolationRemarksMinTypMaxUnitTest voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 16)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17)1220VpeakCreepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmClearance distancePrimary to secondary side6.5mmClearance distancePrimary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmMin Secondary to secondary side12.3mmSecondary to secondary side6.6mmSecondary to secondary side12.3mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side6.6mm		P=1.2W		-7.1		V
Test voltage (50Hz/1s)Primary to secondary side (Note 16) Secondary to secondary side (Note 16)3800 38503900 3900VeffPartial discharge extinction volt.Primary to secondary side (Note 17) Secondary to secondary side (Note 17)1220VpeakCreepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3Primary to secondary side6.6mmSecondary to secondary side12.3mmClearance distancePrimary to secondary side6.6Mary to secondary side6.6mmSecondary to secondary side12.3mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side6.6mm	Gate resistance to COMx			4.7		kΩ
Secondary to secondary side (Note 16)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17)1220VpeakSecondary to secondary side (Note 17)1200VpeakCreepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side12.3mmSecondary to secondary side6.6mm	Electrical Isolation	Remarks	Min	Тур	Max	Unit
Secondary to secondary side (Note 16)380038503900VeffPartial discharge extinction volt.Primary to secondary side (Note 17)1220VpeakSecondary to secondary side (Note 17)1200VpeakCreepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mmSecondary to secondary side6.6mmSecondary to secondary side12.3mmSecondary to secondary side6.6mm	Test voltage (50Hz/1s)	Primary to secondary side (Note 16)	3800	3850	3900	V _{eff}
Partial discharge extinction volt.Primary to secondary side (Note 17)1220VpeakSecondary to secondary side (Note 17)1200VpeakCreepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3Primary to secondary side6.6mmSecondary to secondary side6.6mm			3800	3850	3900	V_{eff}
Secondary to secondary side (Note 17)1200VpeakCreepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3Secondary to secondary side6.6mm	Partial discharge extinction volt.		1220			
Creepage distancePrimary to secondary side12.6mmSecondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mm	·					
Secondary to secondary side6.6mmPrimary to NTC6.5mmClearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mm	Creepage distance					
Primary to NTC6.5mmClearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mm						
Clearance distancePrimary to secondary side12.3mmSecondary to secondary side6.6mm						
Secondary to secondary side 6.6 mm	Clearance distance	-				
Primary to NTC 6.5 mm		Primary to NTC	6.5			

All data refer to $+25^{\circ}$ C and V_{CC} = 15V unless otherwise specified



Footnotes to the Key Data

- 1) The gate current is limited by the gate resistors located on the driver.
- 2) If the specified value is exceeded, this indicates a driver overload. It should be noted that the driver is not protected against overload.
- 3) If the specified value is exceeded, this indicates a driver overload. It should be noted that the driver is not protected against overload. From 70°C to 85°C, the maximum permissible output power can be linearly interpolated from the given data.
- 4) This limit is due to active clamping. Refer to the "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers".
- 5) Undervoltage monitoring of the primary-side supply voltage (VCC to GND). If the voltage drops below this limit, a fault is transmitted to the corresponding outputs and the IGBTs are switched off.
- 6) Undervoltage monitoring of the secondary-side supply voltage (Visox to Veex and Veex to COMx which correspond with the approximate turn-on and turn-off gate-emitter voltages). If the corresponding voltage drops below this limit, the IGBT is switched off and a fault is transmitted to the corresponding output.
- 7) The input impedance can be modified to values $<18 \text{ k}\Omega$ (customer-specific solution).
- 8) Turn-on and turn-off threshold values can be increased (customer-specific solution).
- 9) The resulting pulse width of the direct output of the gate drive unit for short-circuit type I (excluding the delay of the gate resistors) is the sum of response time plus delay to IGBT turn-off.
- 10) The turn-off event of the IGBT is delayed by the specified time after the response time.
- 11) Factory set value. The blocking time can be reduced with an external resistor. Refer to the "Description & Application Manual for 2SP0115T SCALE-2 IGBT Drivers".
- 12) Measured from the transition of the turn-on or turn-off command at the driver input to direct output of the gate drive unit (excluding the delay of the gate resistors).
- 13) Output rise and fall times are measured between 10% and 90% of the nominal output swing with an output load of 10Ω and 40nF. The values are given for the driver side of the gate resistors. The time constant of the output load in conjunction with the present gate resistors leads to an additional delay at the load side of the gate resistors.
- 14) Transmission delay of the fault state from the secondary side to the primary status outputs.
- 15) The gate resistors can be leaded or surface mounted. Power Integrations reserves the right to determine which type will be used. Typically, higher quantities will be produced with SMD resistors and small quantities with leaded resistors.
- 16) HiPot testing (= dielectric testing) must generally be restricted to suitable components. This gate driver is suited for HiPot testing. Nevertheless, it is strongly recommended to limit the testing time to 1s slots as stipulated by EN 50178. Excessive HiPot testing at voltages much higher than 850V_{AC(eff)} may lead to insulation degradation. No degradation has been observed over 1min. testing at 3800V_{AC(eff)}. The transformer of every production sample shipped to customers has undergone 100% testing at the given value or higher (< 5100V_{AC(eff)}) for 1s.
- 17) Partial discharge measurement is performed in accordance with IEC 60270 and isolation coordination specified in EN 50178. The partial discharge extinction voltage between primary and either secondary side is coordinated for safe isolation to EN 50178.
- 18) Jitter measurements are performed with input signals INx switching between 0V and 15V referred to GND, with a corresponding rise time and fall time of 8ns.
- 19) Note that the dead time may vary from sample to sample. A tolerance of approximately ±20% may be expected. If higher timing precisions are required, Power Integrations recommends using direct mode and generating the dead time externally.
- 20) A version with extended operating temperature range of -40°C...85°C (2SP0115T2B0) can also be supplied.
- 21) The storage temperature inside the original package (1) or in case the coating material of coated products may touch external parts (2) must be limited to the given value. Otherwise, it is limited to 90°C.
- 22) The component surface temperature, which may strongly vary depending on the operating condition, must be limited to the given value for coated driver versions to ensure long-term reliability of the coating material.



Legal Disclaimer

The statements, technical information and recommendations contained herein are believed to be accurate as of the date hereof. All parameters, numbers, values and other technical data included in the technical information were calculated and determined to our best knowledge in accordance with the relevant technical norms (if any). They may base on assumptions or operational conditions that do not necessarily apply in general. We exclude any representation or warranty, express or implied, in relation to the accuracy or completeness of the statements, technical information and recommendations contained herein. No responsibility is accepted for the accuracy or sufficiency of any of the statements, technical information, recommendations or opinions communicated and any liability for any direct, indirect or consequential loss or damage suffered by any person arising therefrom is expressly disclaimed.



Ordering Information

Our international terms and conditions of sale apply.

Power Integrations Driver Type #	Related IGBT
2SP0115T2A0-FF900R12ME7_B11 (Temperature range -20°C85°C) 2SP0115T2A0C-FF900R12ME7_B11 (Temperature range -20°C85°C, conformal coating)	FF900R12ME7_B11 FF900R12ME7_B11
Product home page: <u>www.power.com/gate-driver/go/2SP0115T</u>	

Refer to <u>www.power.com/gate-driver/go/nomenclature</u> for information on driver nomenclature

Information about Other Products

For other drivers, evaluation systems product documentation and application support

Please click: www.power.com

© 2009...2019 Power Integrations Switzerland GmbH. All rights reserved. We reserve the right to make any technical modifications without prior notice. Version 1.0 from 2019-11-07



Power Integrations Sales Offices

WORLD HEADQUARTERS

5245 Hellyer Avenue San Jose, CA 95138 USA Tel: +1-408-414-9200 Fax: +1-408-414-9765 Email: <u>usasales@power.com</u>

AMERICAS WEST

5245 Hellyer Avenue San Jose, CA 95138 USA Tel: +1-408-414-8778 Fax: +1-408-414-3760 Email: <u>usasales@power.com</u>

GERMANY (AC-DC/LED Sales) Einsteinring 24 85609 Aschheim, Germany Tel: +49-89-5527-39100 Fax: +49-89-1228-5374 Email: <u>eurosales@power.com</u>

INDIA (Mumbai)

Unit: 106-107, Sagar Tech Plaza-B Sakinaka, Andheri Kurla Road Mumbai, Maharashtra 400072 India Tel 1: +91-22-4003-3700 Tel 2: +91-22-4003-3600 Email: <u>indiasales@power.com</u>

JAPAN

Kosei Dai-3 Bldg. 2-12-11, Shin-Yokohama, Kohoku-ku Yokohama-shi, Kanagawa Japan 222-0033 Tel: +81-45-471-1021 Fax: +81-45-471-3717 Email: japansales@power.com

TAIWAN

5F, No. 318, Nei Hu Rd., Sec. 1 Nei Hu Dist. Taipei, 114 Taiwan Tel: +886-2-2659-4570 Fax: +886-2-2659-4550 Email: <u>taiwansales@power.com</u>

AMERICAS EAST

7360 McGinnis Ferry Road Suite 225 Suwannee, GA 30024 USA Tel: +1-678-957-0724 Fax: +1-678-957-0784 Email: usasales@power.com

CHINA (Shanghai) Room 2410, Charity Plaza No. 88 North Caoxi Road Shanghai, 200030 China Tel: +86-21-6354-6323 Fax: +86-21-6354-6325 Email: <u>chinasales@power.com</u>

GERMANY (Gate Driver Sales) HellwegForum 1 59469 Ense, Germany Tel: +49-2938-64-39990 Email: <u>gate-drivers.sales@power.com</u>

INDIA (New Dehli) #45, Top Floor Okhla Industrial Area, Phase - III New Dehli, 110020 India Tel 1: +91-11-4055-2351 Tel 2: +91-11-4055-2353 Email: indiasales@power.com

KOREA

RM602, 6FL, 22 Teheran-ro 87-gil, Gangnam-gu Seoul, 06164 Korea Tel: +82-2-2016-6610 Fax: +82-2-2016-6630 Email: <u>koreasales@power.com</u>

UNITED KINGDOM

Bulding 5, Suite 21 The Westbrook Centre Milton Road Cambridge, CB4 1YG United Kingdom Tel: +44-7823-557-484 Email: <u>eurosales@power.com</u>

AMERICAS CENTRAL

333 Sheridan Road Winnetka, IL 60093 USA Tel: +1-847-721-6293 Email: <u>usasales@power.com</u>

CHINA (Shenzhen) 17/F, Hivac Building, No 2 Keji South 8th Road, Nanshan District Shenzhen, 518057 China Tel: +86-755-8672-8689 Fax: +86-755-8672-8690 Email: <u>chinasales@power.com</u>

INDIA (Bangalore) #1, 14th Main Road Vasanthangar Bangalore, 560052 India Tel 1: +91-80-4113-8020 Tel 2: +91-80-4113-8028 Fax: +91-80-4113-8023 Email: indiasales@power.com

ITALY

Via Milanese 20 20099 Sesto San Giovanni (MI), Italy Tel: +39-02-4550-8708 Email: <u>eurosales@power.com</u>

SINGAPORE

51 Newton Road #19-01/05 Goldhill Plaza Singapore, 308900 Tel 1: +65-6358-2160 Tel 2: +65-6358-4480 Fax: +65-6358-2015 Email: <u>singaporesales@power.com</u>

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Power Integrations:

2SP0115T2A0C-FF900R12ME7_B11 2SP0115T2A0-CM450DX-34T 2SP0115T2A0-FF900R12ME7_B11